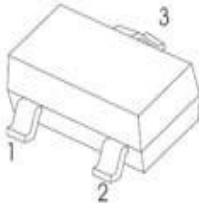
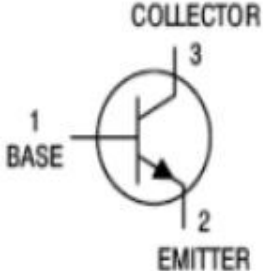


TRANSISTOR (NPN)	SOT-23 Plastic-Encapsulate Transistors		
<p style="text-align: center;"><u>SOT-23</u></p>   <p>1.BASE 2.EMITTER 3.COLLECTOR</p> <p style="text-align: center;">Marking :J3</p>	<p style="text-align: center;">Features</p> <ul style="list-style-type: none"> ※ Complimentary to S9012 ※ Collector Current: $I_c=0.5A$ ※ Excellent Hfe Linearity 		
MAXIMUM RATINGS (Ta=25°C unless otherwise noted)			
Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	40	V
Collector-Emitter Voltage	VCE0	25	V
Emitter-Base Voltage	VEBO	5	V
Collector Current	IC	500	mA
Collector Power Dissipation	PC	300	mW
Thermal Resistance From Junction To Ambient	RθJA	417	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

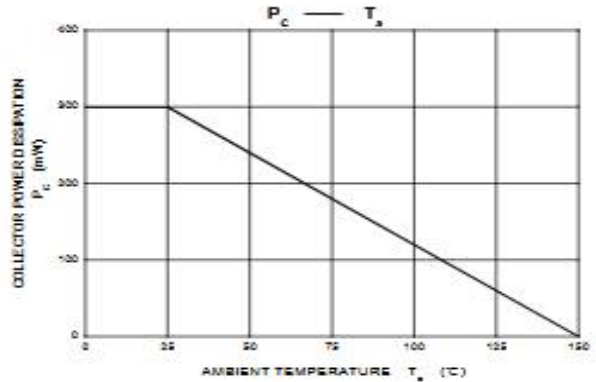
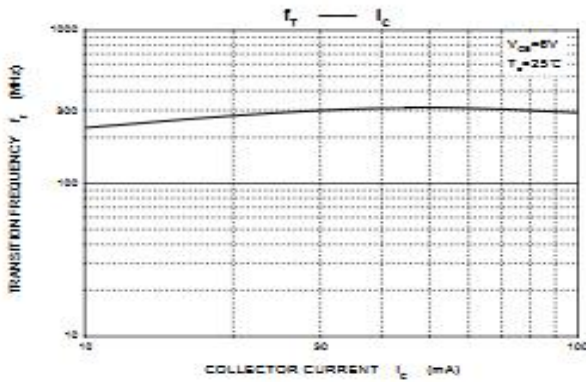
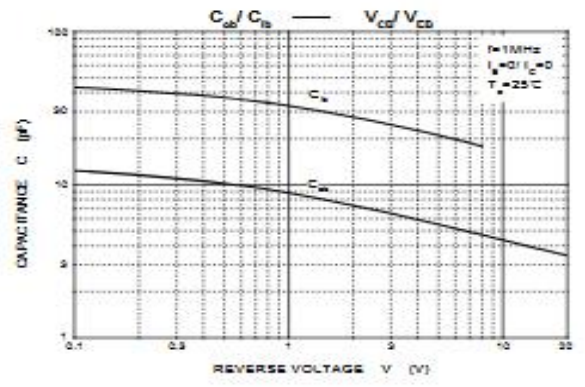
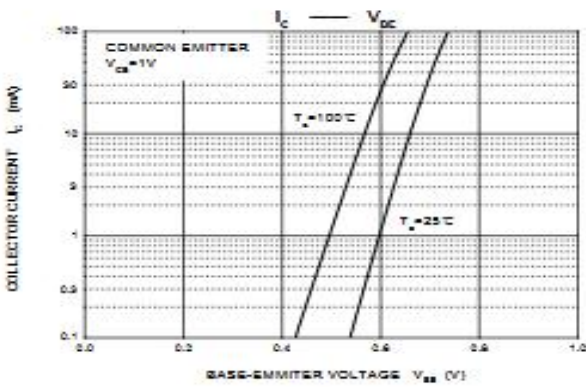
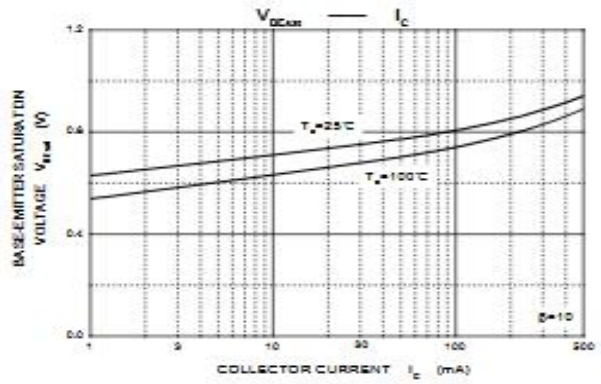
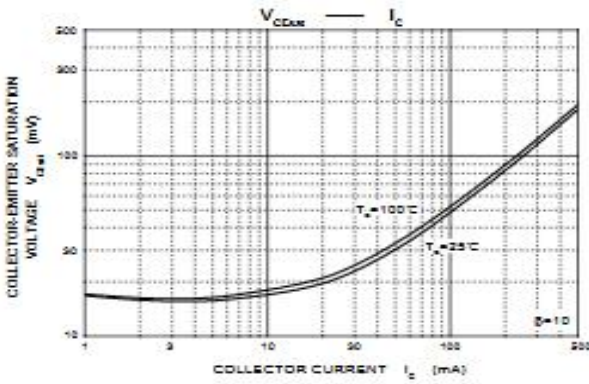
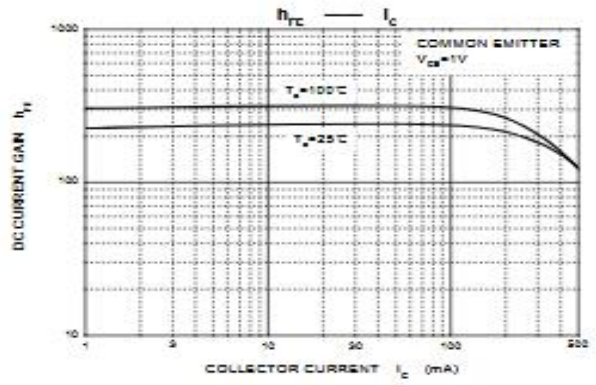
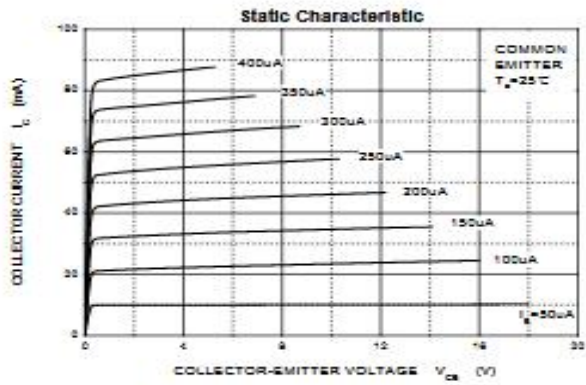
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100 μA, IE=0	40			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	25			V
Emitter-base breakdown voltage	V(BR)EBO	IE=100 μA, IC=0	5			V
Collector cut-off current	ICBO	VCB=40 V , IE=0			0.1	μA
Collector cut-off current	ICEO	VCB=25V , IE=0			0.1	μA
Emitter cut-off current	IEBO	VEB= 5V , IC=0			0.1	μA
DC current gain	hFE	VCE=1V, IC= 50mA	120		400	
	hFE	VCE=1V, IC= 500mA	40			
Collector-emitter saturation voltage	VCE(sat)	IC=500 mA, IB= 50mA			0.6	V
Base-emitter saturation voltage	VBE(sat)	IC=500 mA, IB= 50mA			1.2	V
Transition frequency	fT	VCE=6V, IC=20mA f=30MHz	150			MHz

CLASSIFICATION OF hFI

Rank	L	H	J
Range	120-200	200-350	300-400

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)